

<b>SANYO</b>	No.3439	<h2 style="margin: 0;">2SK1052</h2> <p style="margin: 0;">N-Channel MOS Silicon FET</p> <p style="margin: 0;">Very High-Speed Switching Applications</p>
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**Features**

- Low ON-state resistance.
- Very high-speed switching.

**Absolute Maximum Ratings at Ta = 25°C**

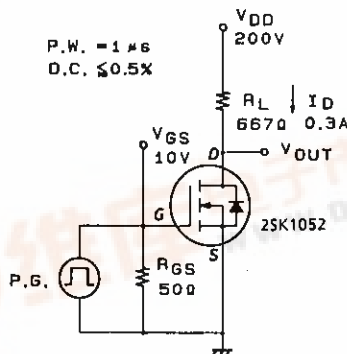
			unit
Drain to Source Voltage	V <sub>DSS</sub>	450	V
Gate to Source Voltage	V <sub>GSS</sub>	±30	V
Drain Current(DC)	I <sub>D</sub>	0.5	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10 μs, duty cycle ≤ 1%	2.0 A
Allowable Power Dissipation	P <sub>D</sub>	Tc = 25°C	30 W
			1.75 W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

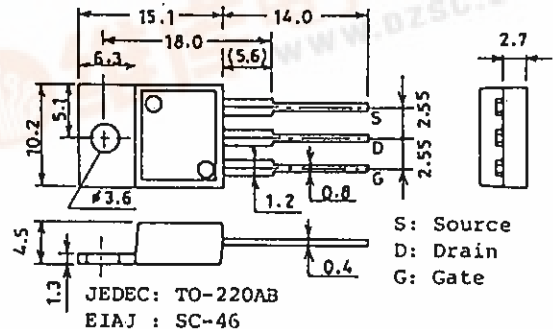
			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	450			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 450V, V <sub>GS</sub> = 0			1.0	mA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0			±100	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	2.0		3.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.3A	0.4	0.8		S
Static Drain to Source on State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 0.3A, V <sub>GS</sub> = 10V		5.5	7.0	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		160		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		25		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		5.0		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	I <sub>D</sub> = 0.3A, V <sub>GS</sub> = 10V V <sub>DD</sub> = 200V, R <sub>GS</sub> = 50Ω		10		ns
Rise Time	t <sub>r</sub>		8		ns	
Turn-OFF Delay Time	t <sub>d(off)</sub>		30		ns	
Fall Time	t <sub>f</sub>		70		ns	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.5A, V <sub>GS</sub> = 0			1.8	V

(Note) Be careful in handling the 2SK1052 because it has no protection diode between gate and source.

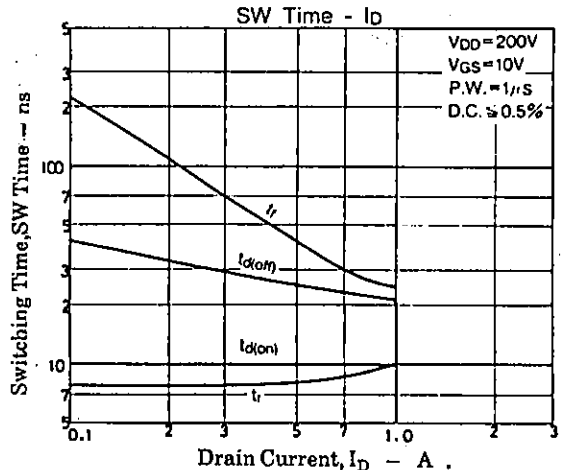
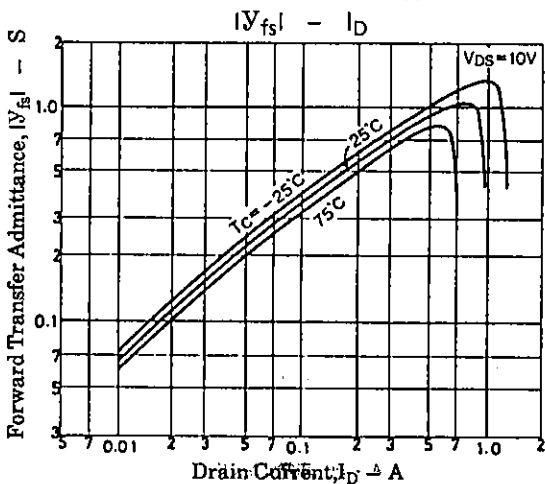
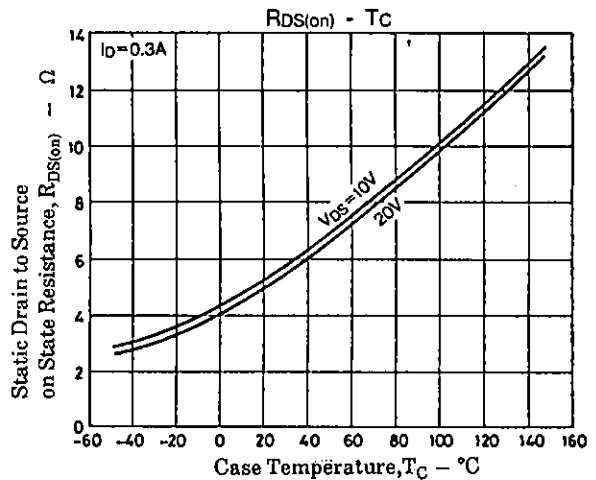
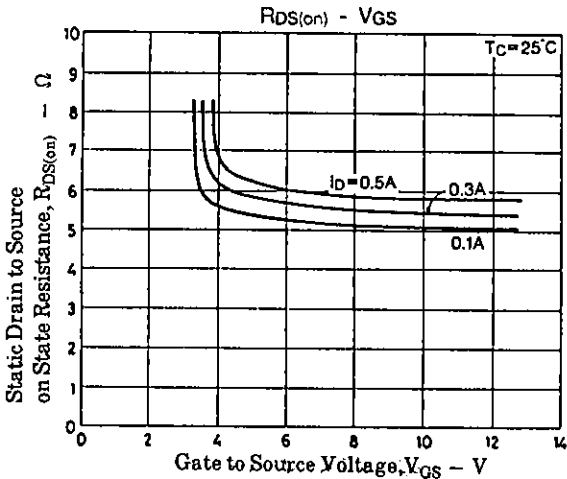
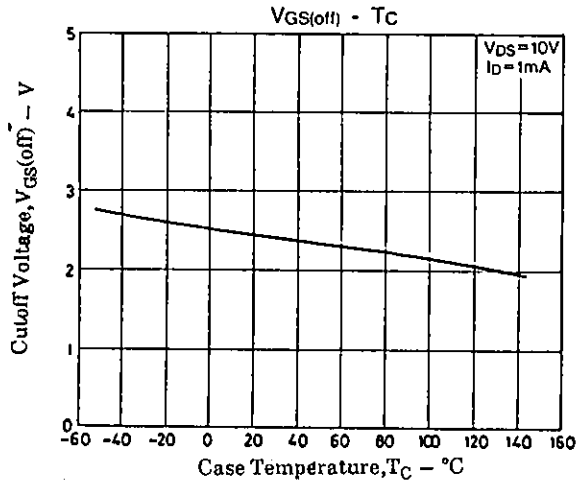
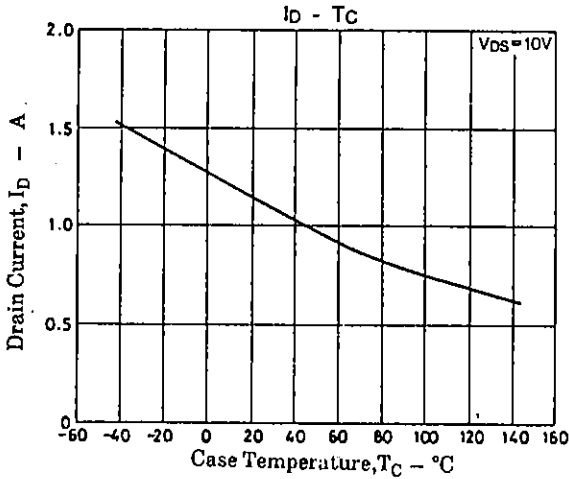
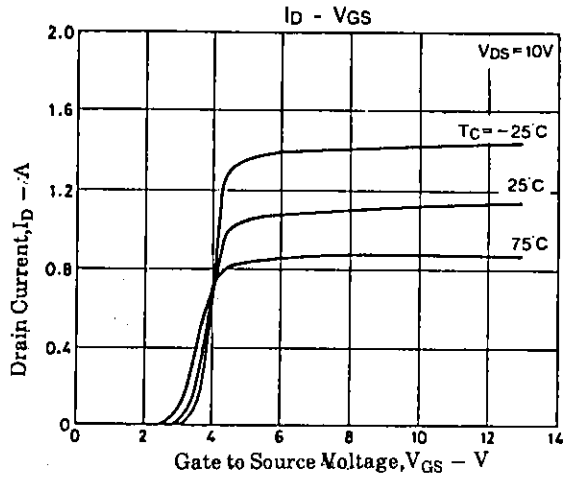
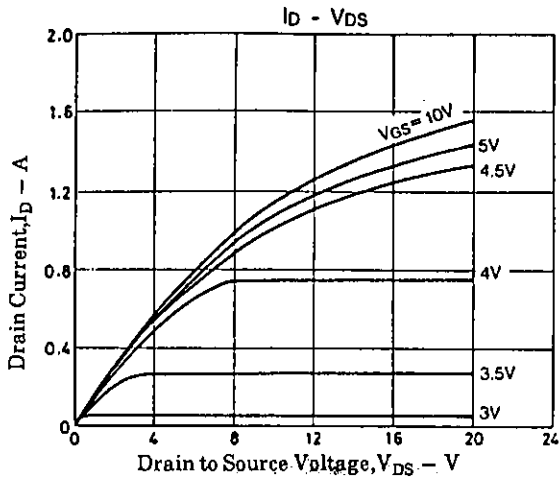
**Switching Time Test Circuit**

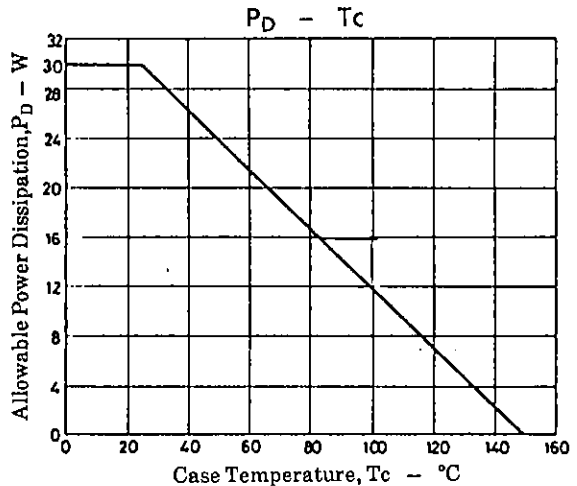
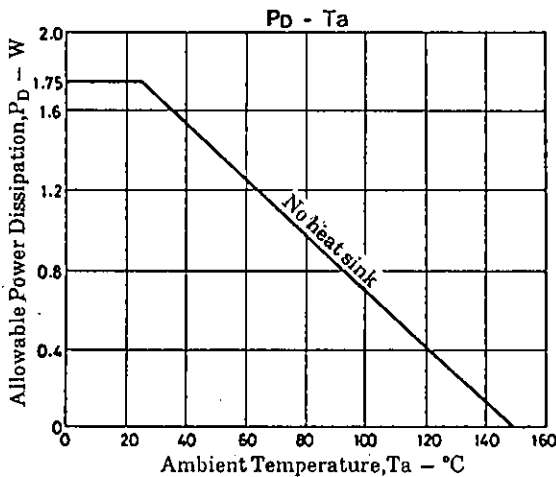
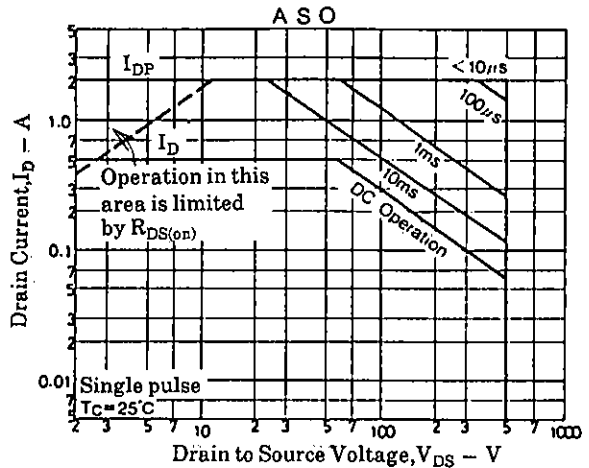
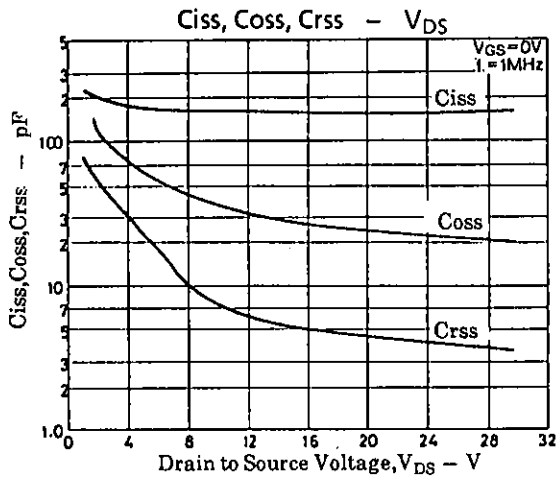


**Package Dimensions 2052B (unit : mm)**



2SK1052





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